

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

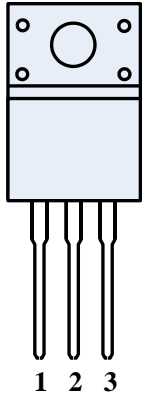
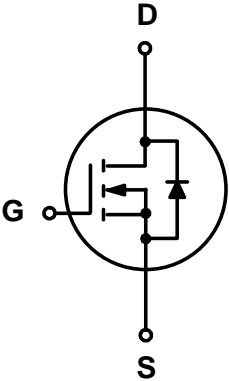
1.2 Applications

- Motor drivers
- DC - DC Converter

1.3 Quick reference

- $BV \geq 100\text{ V}$
- $R_{DS(ON)} \leq 9\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- $P_{tot} \leq 147\text{ W}$
- $R_{DS(ON)} \leq 13\text{ m}\Omega @ V_{GS} = 6\text{ V}$
- $I_D \leq 60\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate (G)		
2	Drain (D)		
3	Source (S)		
		<p>Top View</p> <p>TO-220-3L</p>	



3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	Drain-Source Voltage	T _C = 25 °C	100	-	V
V _{GS}	Gate-Source Voltage	T _C = 25 °C	-	± 20	V
I _D ^{*,***}	Drain Current (DC)	T _C = 25 °C, V _{GS} = 10 V	-	60	A
I _D [*]		T _C = 100 °C, V _{GS} = 10 V	-	54	A
I _{DM} ^{*,**,***}	Drain Current (Pulsed)	T _C = 25 °C, V _{GS} = 10 V	-	120	A
P _{tot} [*]	Total Power Dissipation	T _C = 25 °C	-	147	W
T _{stg}	Storage Temperature		- 55	150	°C
T _J	Junction Temperature		-	150	°C
I _S	Diode Forward Current	T _C = 25 °C	-	60	A
E _{AS} [*]	Single Pulsed Avalanche Energy	V _{DD} = 50 V, L= 1 mH	-	128	mJ
R _{θJA} [*]	Thermal Resistance- Junction to Ambient		-	62.5	°C / W
R _{θJC} [*]	Thermal Resistance- Junction to Case		-	0.85	

Notes :

- * Surface Mounted on 1 in² pad area, t ≤ 10 sec
- ** Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ0810C	<div style="display: inline-block; border: 1px solid black; padding: 2px;">0810 YWWXXX</div> YWWXXX: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ0810C	TO220C				

Note: KUAJIJIXIN defines " Green " as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)



6. Electrical Characteristics (T_A = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	100	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = 250 μA	1	-	3	V
I _{DSS}	Zero Gate Voltage Source Current	V _{DS} = 80 V, V _{GS} = 0 V T _J = 85 °C	-	-	1	μA
			-	-	30	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 20 V, V _{DS} = 0 V	-	-	± 100	nA
R _{DS(ON)} ^a	Drain-Source On-State Resistance	V _{GS} = 10 V, I _D = 20 A	-	8.2	9	mΩ
	Drain-Source On-State Resistance	V _{GS} = 6 V, I _D = 15 A	-	10.8	13	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} = 20 A, V _{GS} = 0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} = 20 A, dI _{SD} /dt = 100 A/μs	-	60	-	nS
Q _{rr}	Reverse Recovery Charge		-	83	-	nC
Dynamic Characteristics^b						
C _{iss}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 50 V Frequency = 1 MHz	-	2211	-	pF
C _{oss}	Output Capacitance		-	339	-	
C _{rss}	Reverse Transfer Capacitance		-	54	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} = 50 V, V _{GEN} = 10 V, R _G = 4.5 Ω, R _L = 2.5 Ω, I _D = 20 A	-	12	-	nS
t _r	Turn-on Rise Time		-	40	-	
t _{d(off)}	Turn-off Delay Time		-	29	-	
t _f	Turn-off Fall Time		-	40	-	
Gate Charge Characteristics^b						
Q _g	Total Gate Charge	V _{GS} = 10 V, V _{DS} = 50 V, I _{DS} = 20 A	-	44	-	nC
Q _{gs}	Gate-Source Charge		-	13	-	
Q _{gd}	Gate-Drain Charge		-	14	-	

Notes :

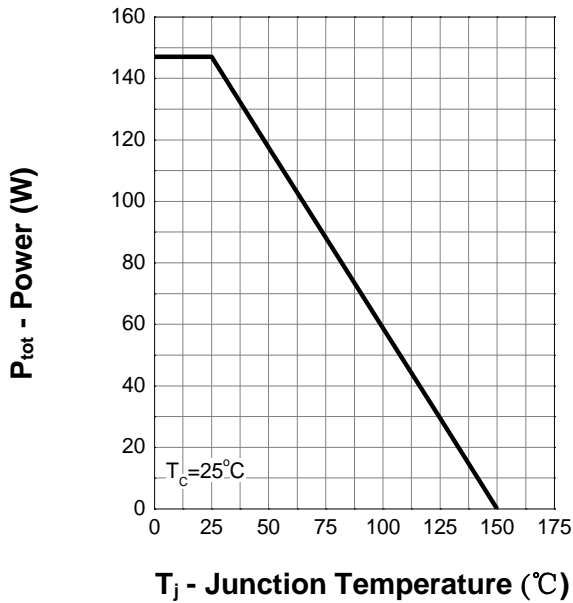
a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2 %

b : Guaranteed by design, not subject to production testing

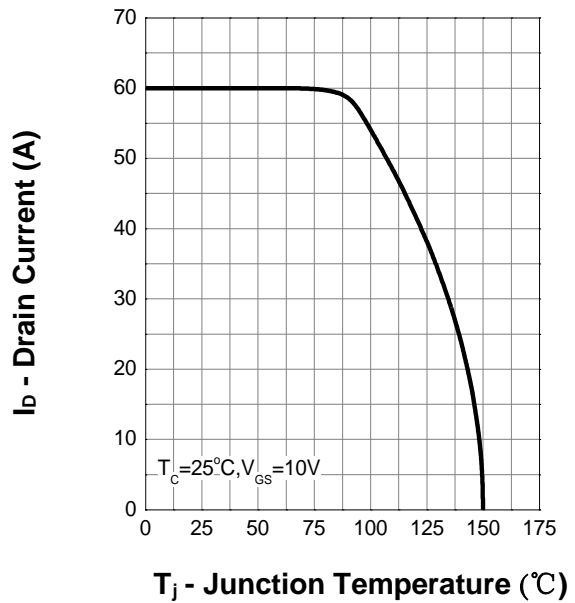


7. Typical Characteristics

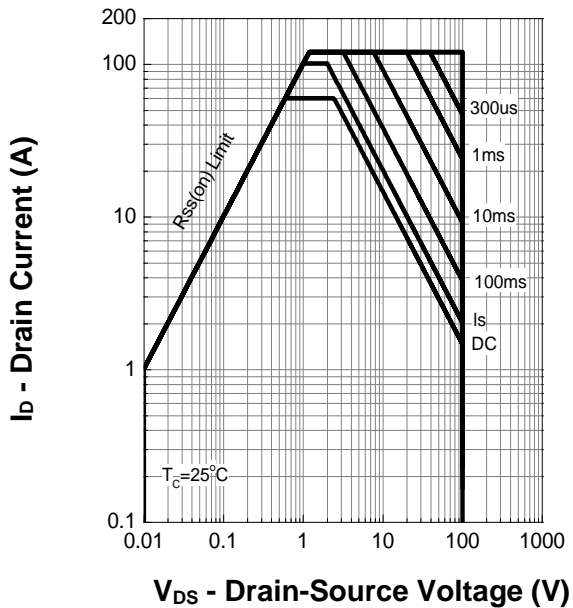
Power Capability



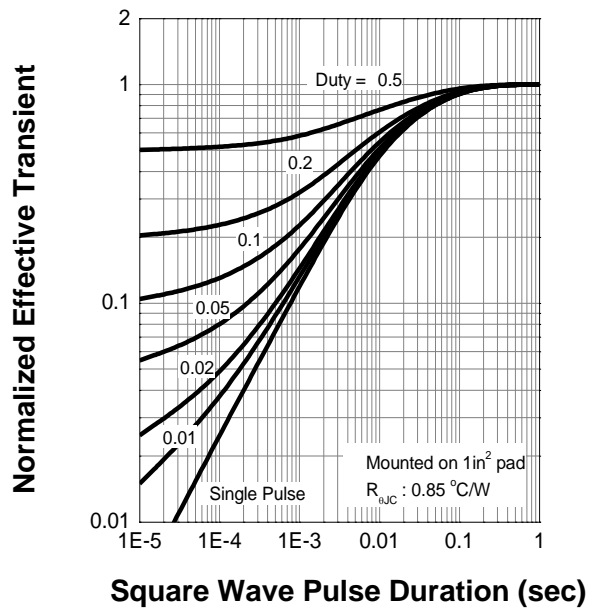
Current Capability



Safe Operating Area



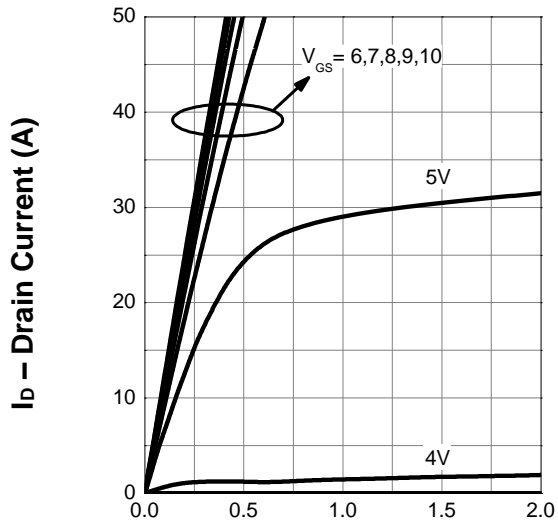
Thermal Transient Impedance





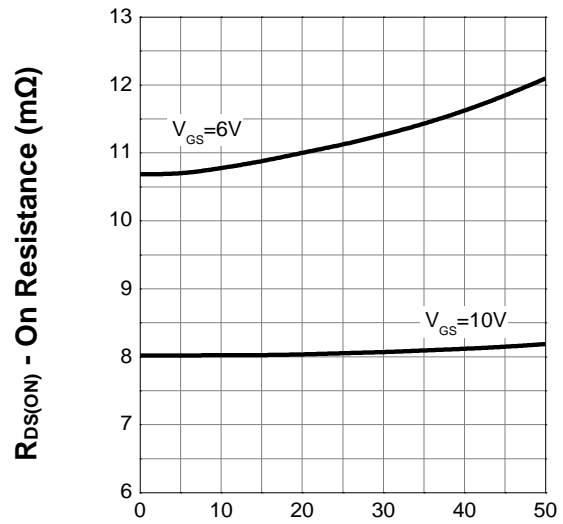
7. Typical Characteristics (cont.)

Output Characteristics



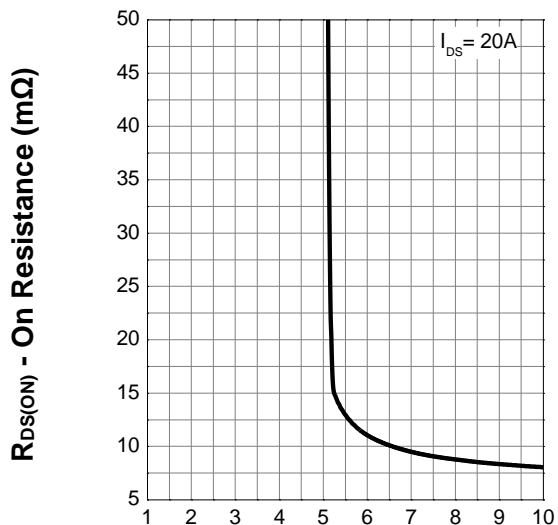
V_{DS} - Drain-Source Voltage (V)

Drain-Source On Resistance



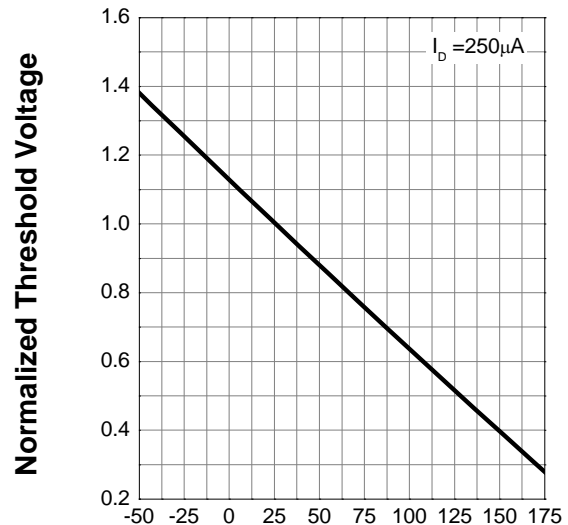
I_D - Drain Current (A)

Transfer Characteristics



V_{GS} - Gate-Source Voltage (V)

Gate Threshold Voltage

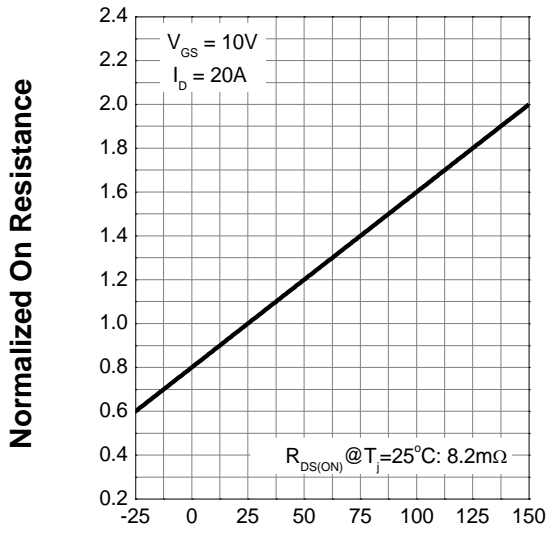


T_j - Junction Temperature ($^{\circ}C$)

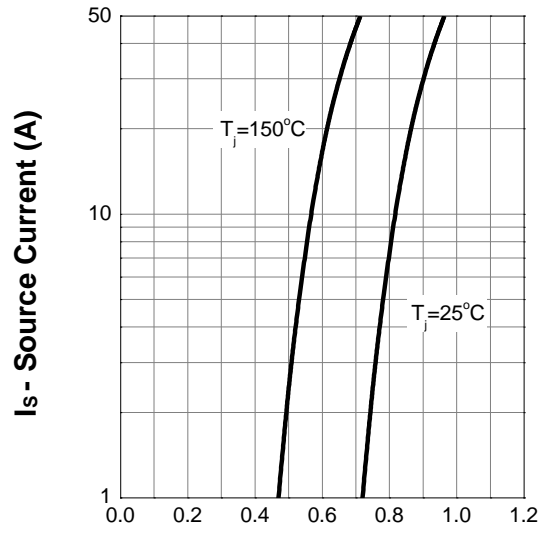


7. Typical Characteristics (cont.)

Drain-Source On Resistance



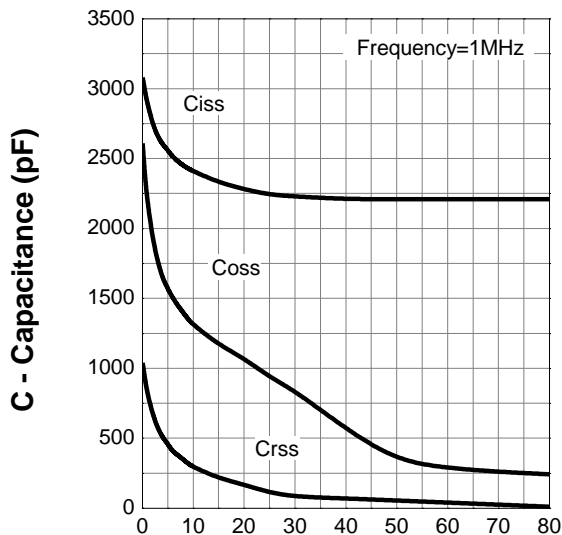
Body Diode Characteristics



T_j - Junction Temperature ($^\circ C$)

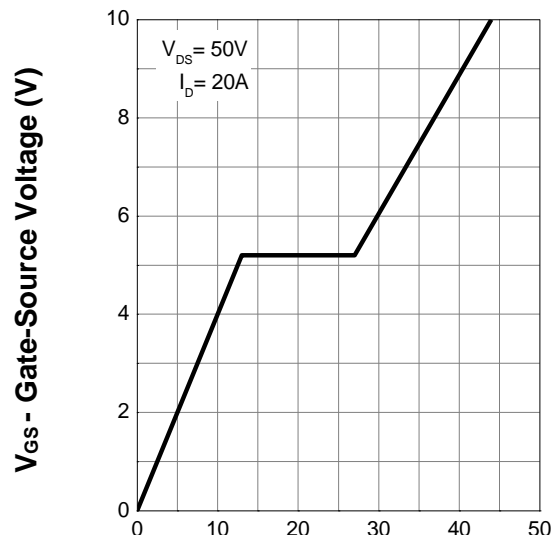
V_{SD} - Source-Drain Voltage (V)

Capacitance



V_{DS} - Drain-Source Voltage (V)

Gate Charge



Q_G - Gate Charge (nC)

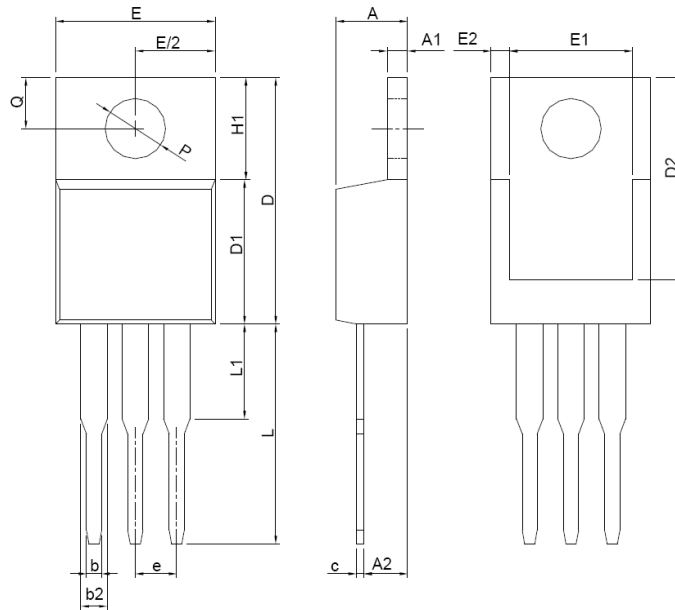


快捷冠

KJ0810C

8. Package Dimensions

TO-220-3L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	3.56	4.83
A1	0.51	1.40
A2	2.03	2.92
b	0.38	1.02
b2	1.14	1.78
c	0.36	0.61
D	14.22	16.51
D1	8.38	9.02
D2	12.19	12.88
E	9.65	10.67
E1	6.86	8.89
E2	0.76BSC	
e	2.54BSC	
H1	5.84	6.86
L	12.70	14.73
L1	6.35BSC	
P	3.53	4.09
Q	2.54	3.43